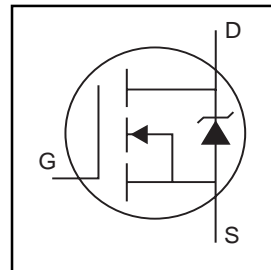


- Advanced Process Technology
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Drop in Replacement of the IRFZ48 for Linear/Audio Applications

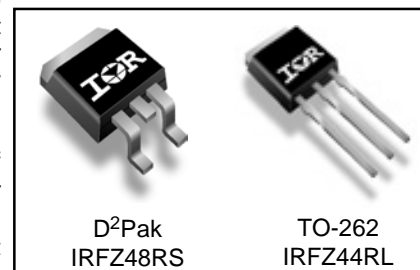


| |
|----------------------------|
| $V_{DSS} = 60V$ |
| $R_{DS(on)} = 0.018\Omega$ |
| $I_D = 50^*A$ |

Description

Advanced HEXFET® Power MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The D²Pak is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D²Pak is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0W in a typical surface mount application.



Absolute Maximum Ratings

| | Parameter | Max. | Units |
|---------------------------|------------------------------------------|------------------------|-------|
| $I_D @ T_C = 25^\circ C$ | Continuous Drain Current, $V_{GS} @ 10V$ | 50* | A |
| $I_D @ T_C = 100^\circ C$ | Continuous Drain Current, $V_{GS} @ 10V$ | 50* | |
| I_{DM} | Pulsed Drain Current ① | 290 | |
| $P_D @ T_C = 25^\circ C$ | Power Dissipation | 190 | W |
| | Linear Derating Factor | 1.3 | W/°C |
| V_{GS} | Gate-to-Source Voltage | ± 20 | V |
| E_{AS} | Single Pulse Avalanche Energy② | 100 | mJ |
| dv/dt | Peak Diode Recovery dv/dt ③ | 4.5 | V/ns |
| T_J | Operating Junction and | -55 to + 175 | °C |
| T_{STG} | Storage Temperature Range | | |
| | Soldering Temperature, for 10 seconds | 300 (1.6mm from case) | |
| | Mounting torque, 6-32 or M3 screw | 10 lbf•in (1.1N•m) | |

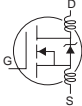
Thermal Resistance

| | Parameter | Typ. | Max. | Units |
|-----------------|-------------------------------------|------|------|-------|
| $R_{\theta JC}$ | Junction-to-Case | — | 0.8 | °C/W |
| $R_{\theta CS}$ | Case-to-Sink, Flat, Greased Surface | 0.50 | — | |
| $R_{\theta JA}$ | Junction-to-Ambient | — | 62 | |

IRFZ48RS/IRFZ48RL

International
IR Rectifier

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|---------------------------------|--------------------------------------|------|-------|-------|----------|--------------------------------------------------------------------------------------|
| $V_{(BR)DSS}$ | Drain-to-Source Breakdown Voltage | 60 | — | — | V | $V_{GS} = 0V, I_D = 250\mu A$ |
| $\Delta V_{(BR)DSS}/\Delta T_J$ | Breakdown Voltage Temp. Coefficient | — | 0.060 | — | V/°C | Reference to $25^\circ\text{C}, I_D = 1\text{mA}$ |
| $R_{DS(on)}$ | Static Drain-to-Source On-Resistance | — | — | 0.018 | Ω | $V_{GS} = 10V, I_D = 43A$ ④ |
| $V_{GS(th)}$ | Gate Threshold Voltage | 2.0 | — | 4.0 | V | $V_{DS} = V_{GS}, I_D = 250\mu A$ |
| g_{fs} | Forward Transconductance | 27 | — | — | S | $V_{DS} = 25V, I_D = 43A$ ④ |
| I_{DSS} | Drain-to-Source Leakage Current | — | — | 25 | μA | $V_{DS} = 60V, V_{GS} = 0V$ |
| | | — | — | 250 | | $V_{DS} = 48V, V_{GS} = 0V, T_J = 150^\circ\text{C}$ |
| I_{GSS} | Gate-to-Source Forward Leakage | — | — | 100 | nA | $V_{GS} = 20V$ |
| | Gate-to-Source Reverse Leakage | — | — | -100 | | $V_{GS} = -20V$ |
| Q_g | Total Gate Charge | — | — | 110 | nC | $I_D = 72A$ |
| Q_{gs} | Gate-to-Source Charge | — | — | 29 | | $V_{DS} = 48V$ |
| Q_{gd} | Gate-to-Drain ("Miller") Charge | — | — | 36 | | $V_{GS} = 10V$, See Fig. 6 and 13 ④ |
| $t_{d(on)}$ | Turn-On Delay Time | — | 8.1 | — | ns | $V_{DD} = 30V$ |
| t_r | Rise Time | — | 250 | — | | $I_D = 72A$ |
| $t_{d(off)}$ | Turn-Off Delay Time | — | 210 | — | | $R_G = 9.1\Omega$ |
| t_f | Fall Time | — | 250 | — | | $R_D = 0.34\Omega$, See Fig. 10 ④ |
| L_D | Internal Drain Inductance | — | 4.5 | — | nH | Between lead, 6mm (0.25in.) from package and center of die contact |
| L_S | Internal Source Inductance | — | 7.5 | — | |  |
| C_{iss} | Input Capacitance | — | 2400 | — | pF | $V_{GS} = 0V$ |
| C_{oss} | Output Capacitance | — | 1300 | — | | $V_{DS} = 25V$ |
| C_{riss} | Reverse Transfer Capacitance | — | 190 | — | | $f = 1.0\text{MHz}$, See Fig. 5 |

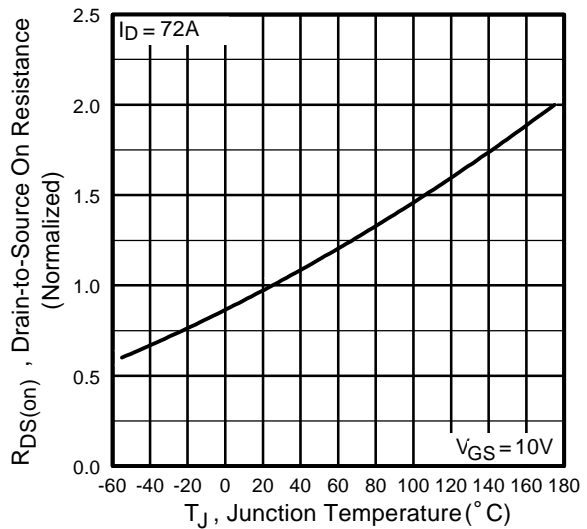
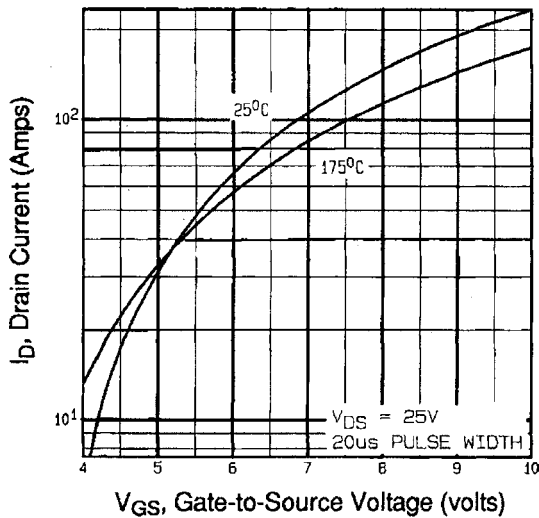
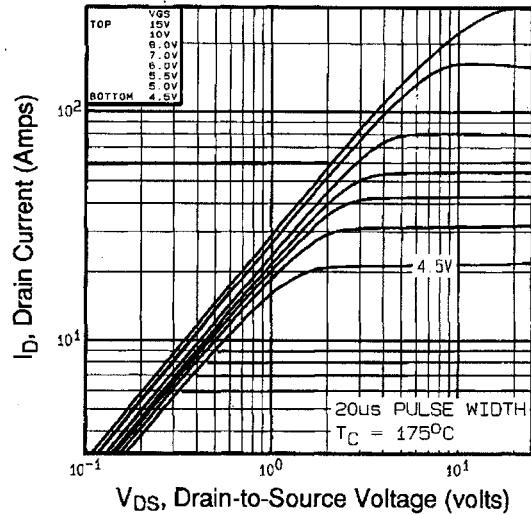
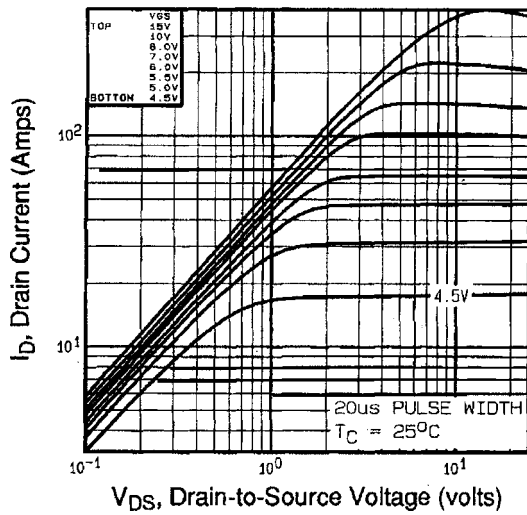
Source-Drain Ratings and Characteristics

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|----------|-------------------------------------------|---------------------------------------------------------------------------|------|------|---------|-------------------------------------------------------------------------|
| I_S | Continuous Source Current (Body Diode) | — | — | 50* | A | MOSFET symbol showing the integral reverse p-n junction diode. |
| I_{SM} | Pulsed Source Current (Body Diode)① | — | — | 290 | | |
| V_{SD} | Diode Forward Voltage | — | — | 2.0 | V | $T_J = 25^\circ\text{C}, I_S = 72A, V_{GS} = 0V$ ④ |
| t_{rr} | Reverse Recovery Time | — | 120 | 180 | ns | $T_J = 25^\circ\text{C}, I_F = 72A$ |
| Q_{rr} | Reverse Recovery Charge | — | 0.50 | 0.80 | μC | $di/dt = 100A/\mu s$ ④ |
| t_{on} | Forward Turn-On Time | Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D) | | | | |

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② $V_{DD} = 25V$, Starting $T_J = 25^\circ\text{C}$, $L = 22\mu H$
 $R_G = 25\Omega, I_{AS} = 72A$. (See Figure 12)
- ③ $I_{SD} \leq 72A, di/dt \leq 200A/\mu s, V_{DD} \leq V_{(BR)DSS}, T_J \leq 175^\circ\text{C}$
- ④ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.

* Current limited by the package, (Die Current = 72A)



IRFZ48RS/IRFZ48RL

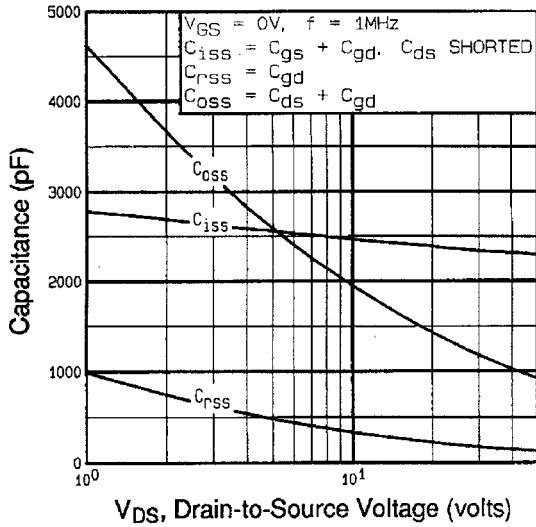


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

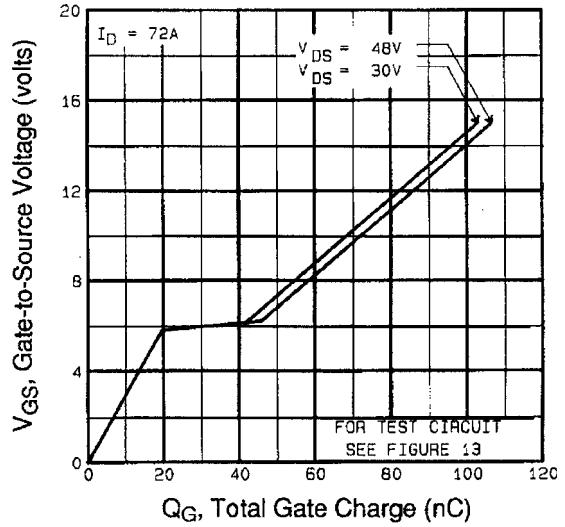


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

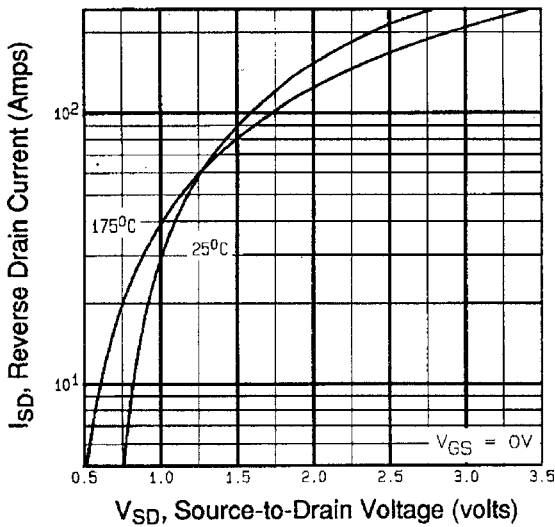


Fig 7. Typical Source-Drain Diode Forward Voltage

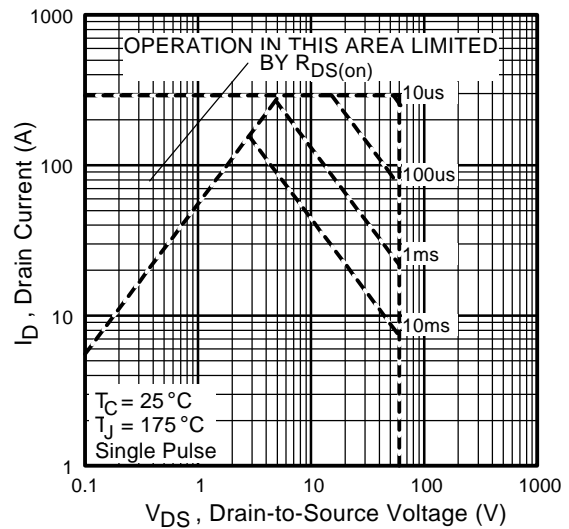


Fig 8. Maximum Safe Operating Area

IRFZ48RS/IRFZ48RL

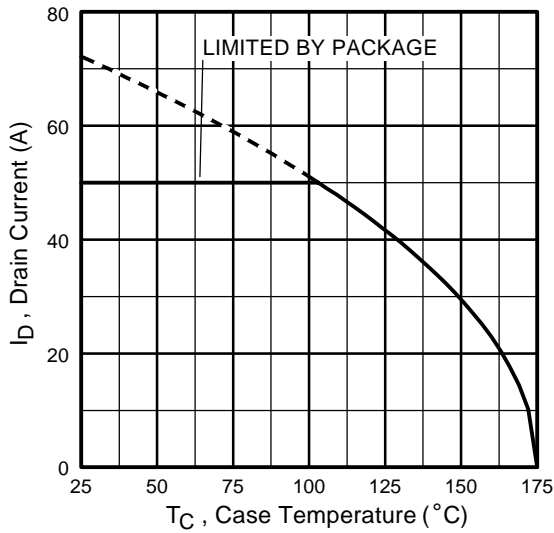


Fig 9. Maximum Drain Current Vs. Case Temperature

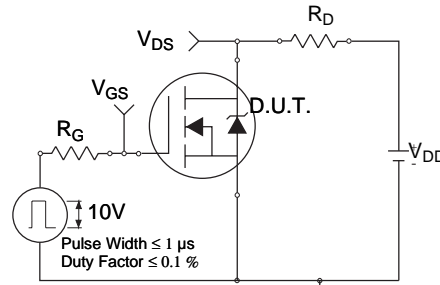


Fig 10a. Switching Time Test Circuit

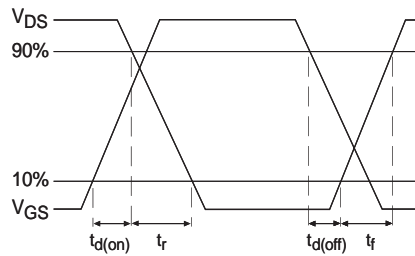


Fig 10b. Switching Time Waveforms

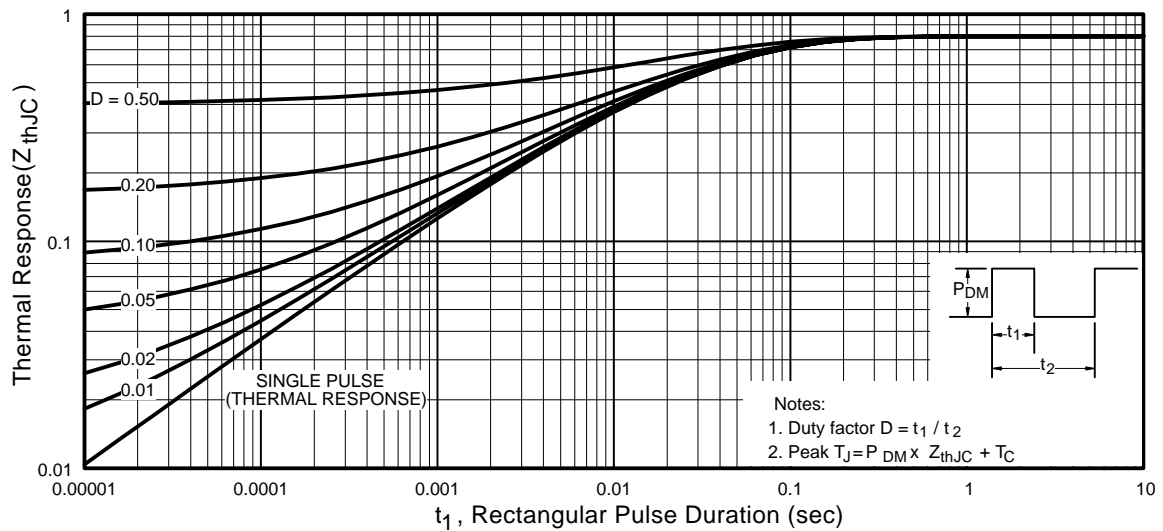


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

IRFZ48RS/IRFZ48RL

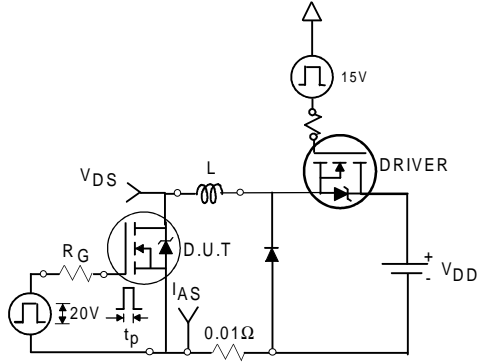


Fig 12a. Unclamped Inductive Test Circuit



Fig 12b. Unclamped Inductive Waveforms

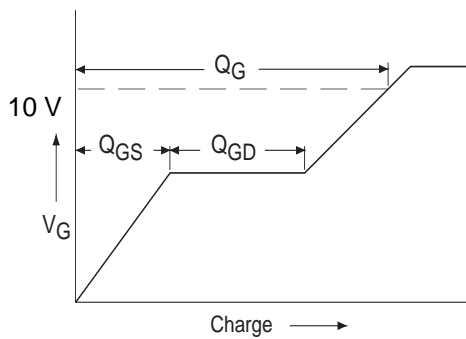


Fig 13a. Basic Gate Charge Waveform

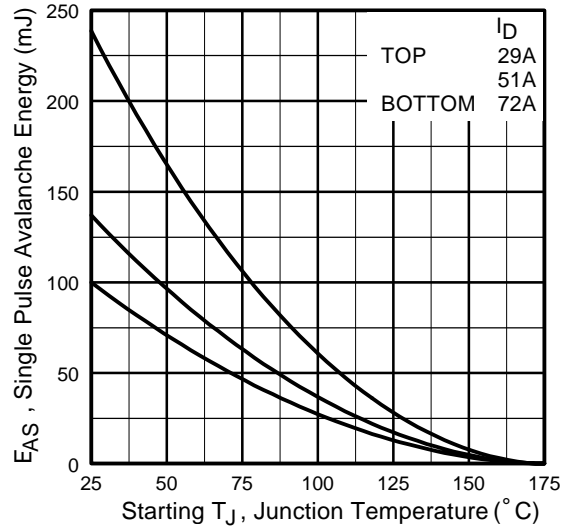


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

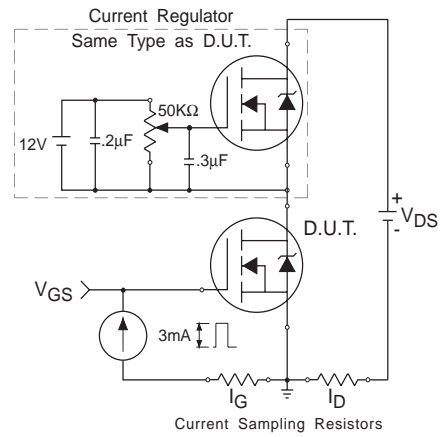
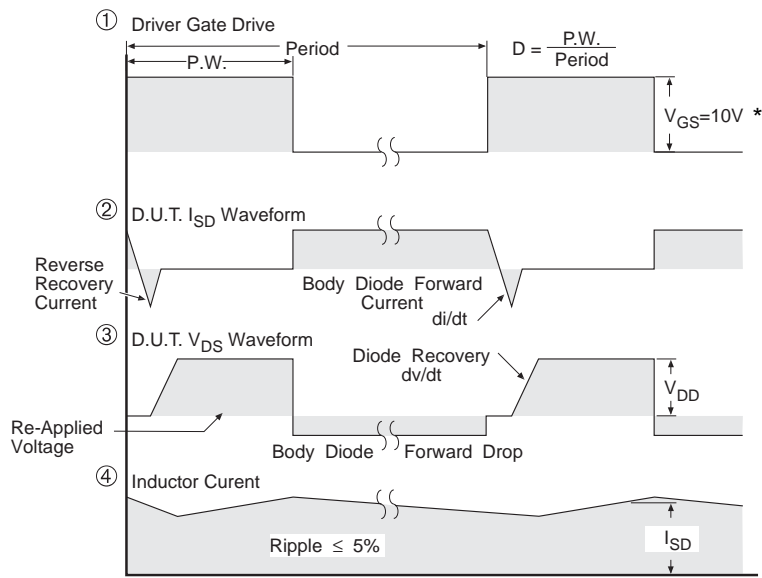
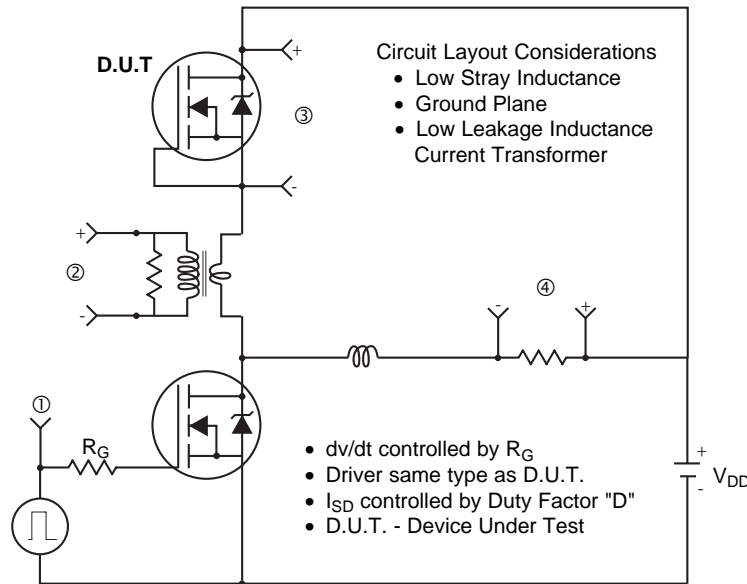


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



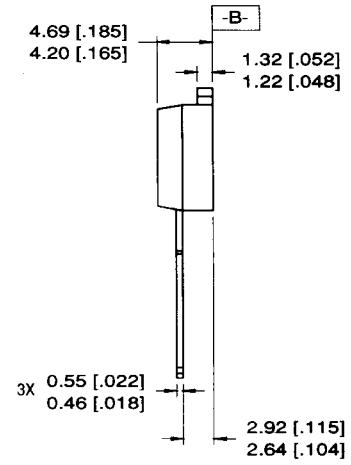
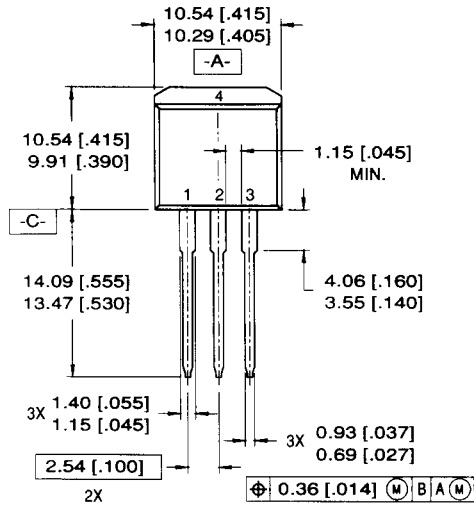
* $V_{GS} = 5V$ for Logic Level Devices

Fig 14. For N-Channel HEXFETS

IRFZ48RS/IRFZ48RL



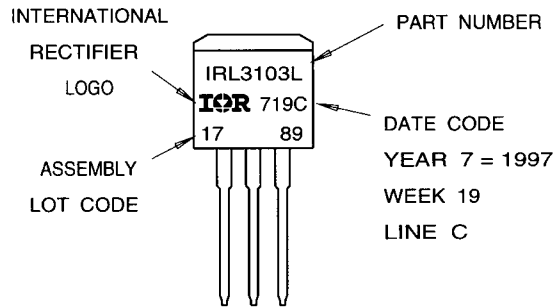
TO-262 Package Outline



- NOTES:
1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1982
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
 4. HEATSINK & LEAD DIMENSIONS DO NOT INCLUDE BURRS.

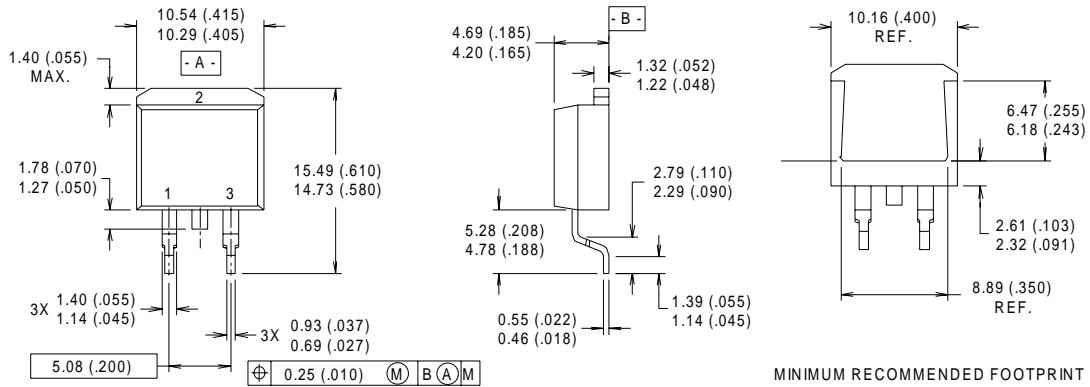
TO-262 Part Marking Information

EXAMPLE: THIS IS AN IRL3103L
 LOT CODE 1789
 ASSEMBLED ON WW 19, 1997
 IN THE ASSEMBLY LINE "C"



D²Pak Package Outline

Dimensions are shown in millimeters (inches)



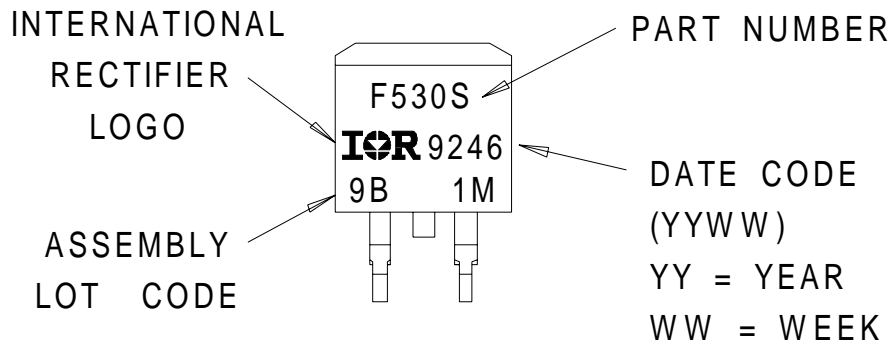
NOTES:

- 1 DIMENSIONS AFTER SOLDER DIP.
- 2 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
- 3 CONTROLLING DIMENSION : INCH.
- 4 HEATSINK & LEAD DIMENSIONS DO NOT INCLUDE BURRS.

LEAD ASSIGNMENTS

- 1 - GATE
- 2 - DRAIN
- 3 - SOURCE

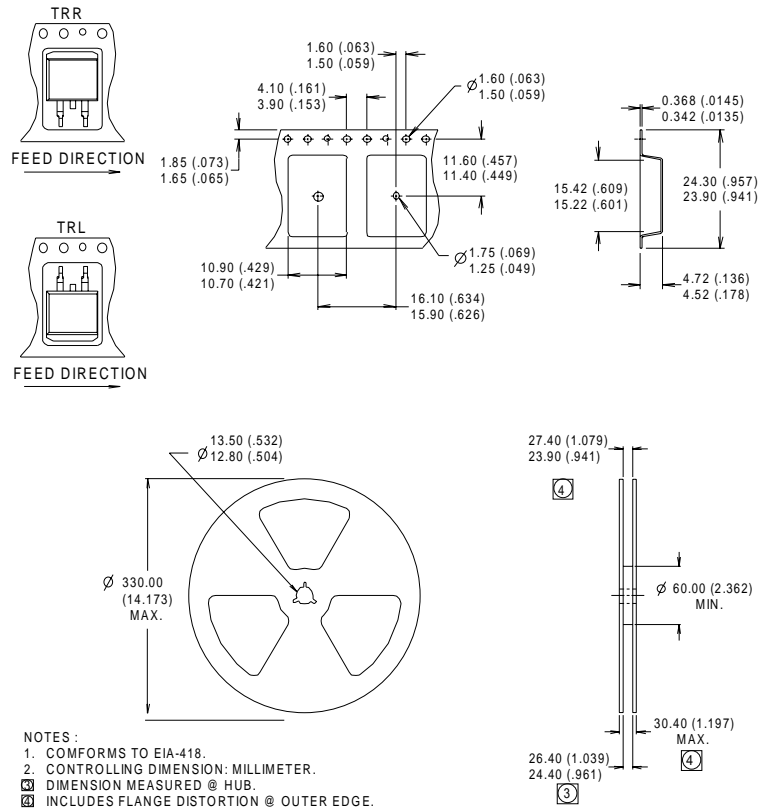
D²Pak Part Marking Information



IRFZ48RS/IRFZ48RL



D²Pak Tape & Reel Information



Data and specifications subject to change without notice.
 This product has been designed and qualified for the Industrial market.
 Qualification Standards can be found on IR's Web site.



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